



## **COMET SEE Tools 13-12-2022**

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# Classical SEE rate estimation : ions, CREME

Cosmic Rays Effects on MicroElectronics

NRL, 1986 updated 1996 (but not the rate estimation technique)

Based on energy deposition into a “sensitive volume” (SV)

SV taken as a rectangular parallelepiped

Deposited energy  $E_d \rightarrow$  Deposited charge  $Q_d$

Compared with critical charge  $Q_c$  :  $Q_d > Q_c \rightarrow$  SEE

All species / energies folded into a unique LET spectrum

$LET = 1/\rho \, dE/dx$  where  $\rho$  = volumic mass, usual unit  $MeV/mg/cm^2$

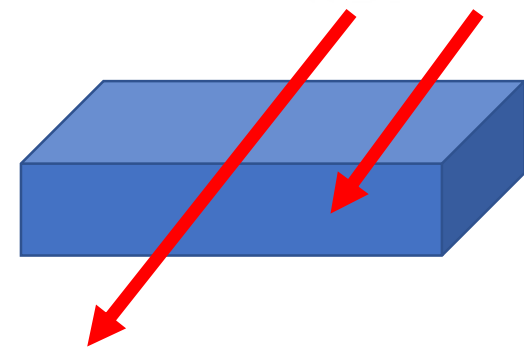
$E_d \sim LET \times z$  where  $z$  = path length into SV

Calculation made over cross-section vs LET curve

$Q_c$  determined by threshold  $LET \times SV$  thickness

## Advantages :

- Simple and fast calculation
- One unique physical value : LET



## Disadvantages :

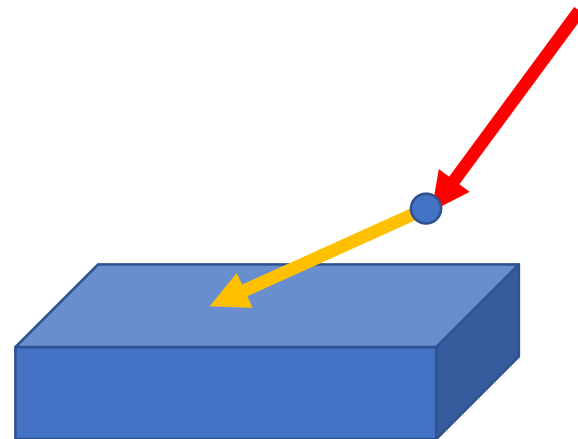
- Arbitrary parameters such as SV geometry, thickness, number of SVs
- LET may vary along path length
- Ion track is unidimensional
- Collected charge vs deposited charge

# Classical SEE rate estimation : protons

Indirect ionization through recoil atoms generated by proton – target atom nuclear reaction : analog to an ion source inside the device

Direct convolution of proton energy spectrum with cross-section vs Energy curve (implicit hypothesis : recoils are emitted in all directions)

Techniques to reconstruct proton cross-section from heavy ion cross sections (PROFIT, SIMPA, METIS,...)



## Advantages :

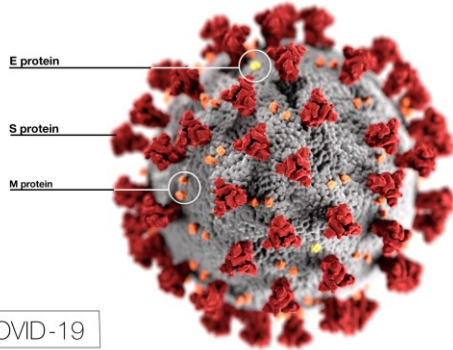
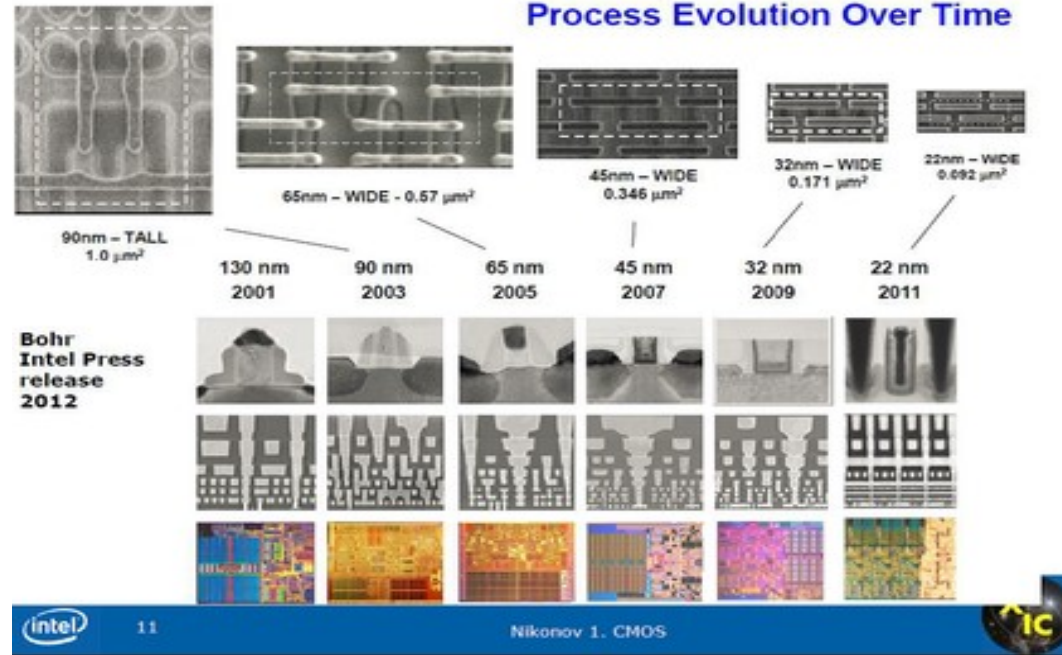
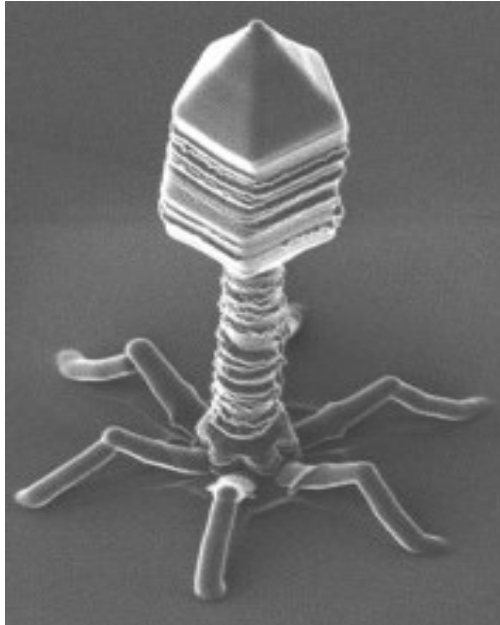
- Simple and fast calculation
- Few arbitrary hypothesis & parameters
- Works well against flight data

## Disadvantages :

- Some fixed parameters into some reconstruction codes
- Usually only Si recoils
- Only the heaviest recoil atom

# Dimensions

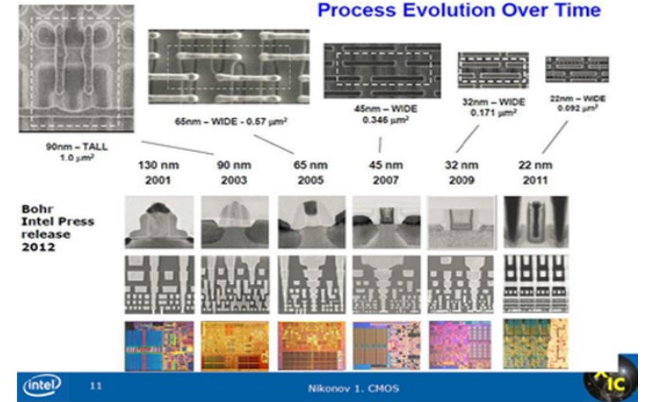
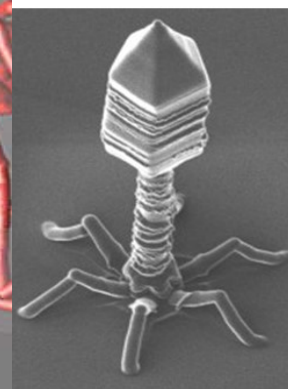
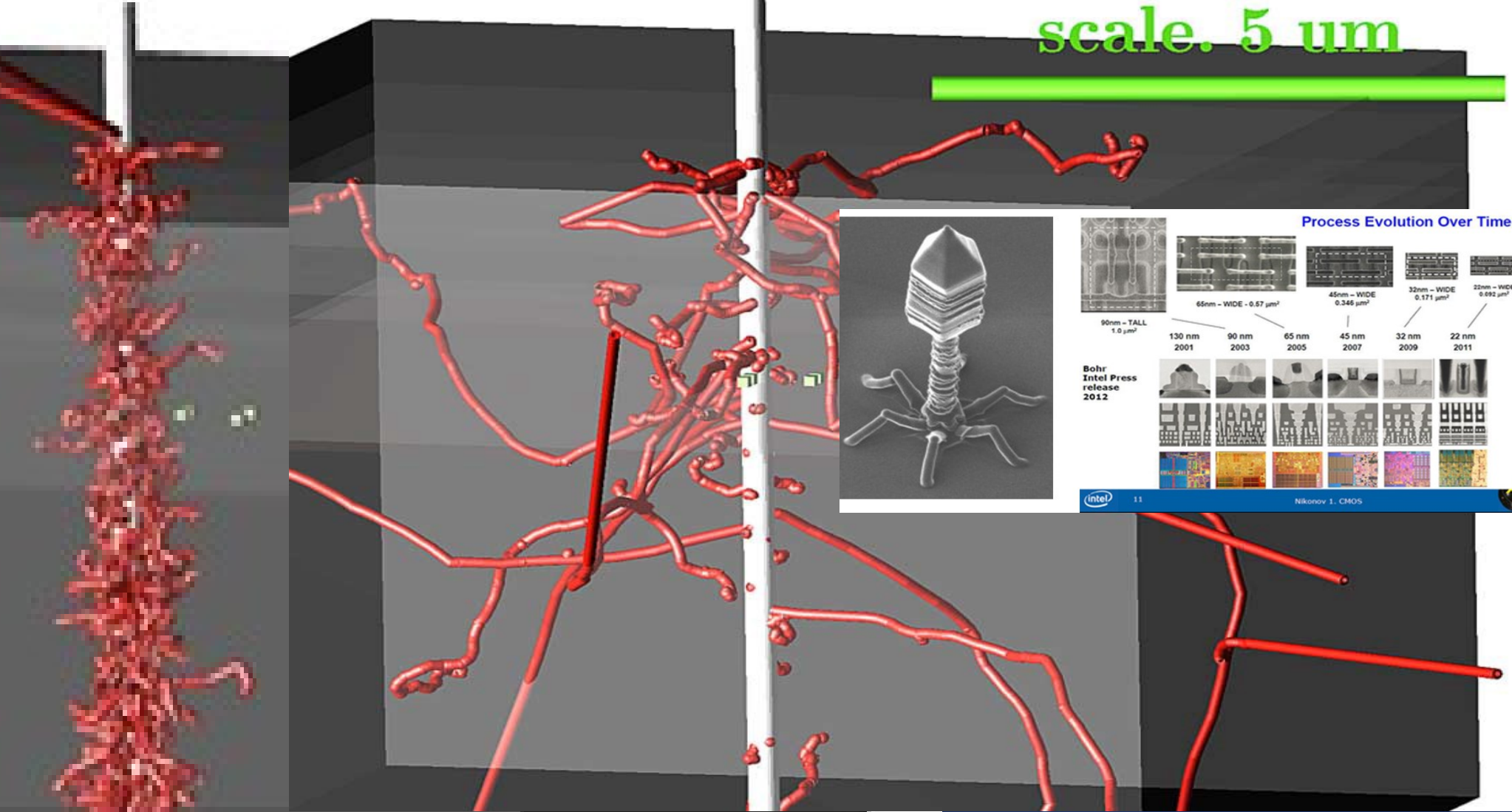
About the same scale of structuration than elementary living matter



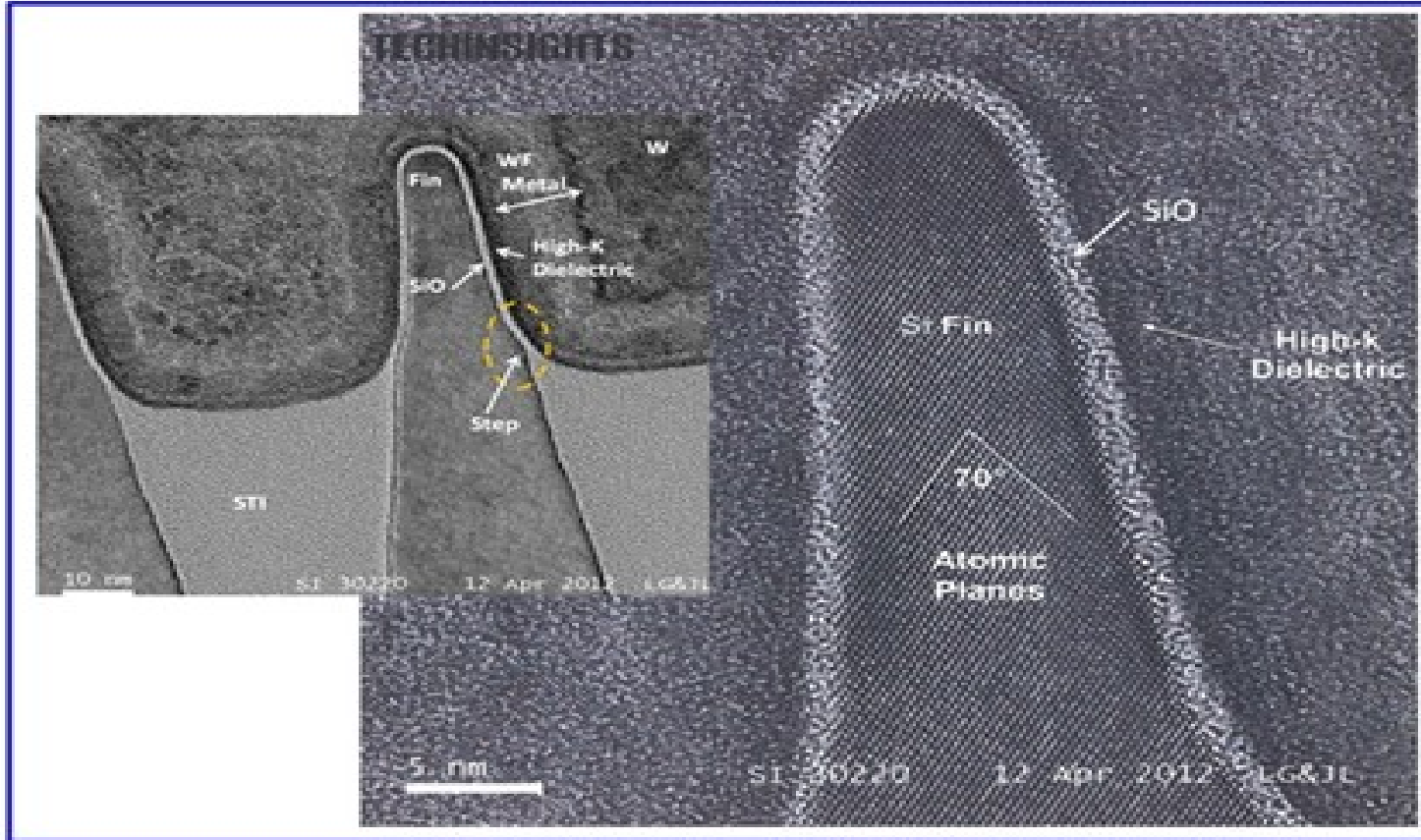
The bacteriophage virus is about 200 nm tall and 65 nm wide. SARS-COV2 about 125 nm.

# Compared dimensions

scale. 5 um

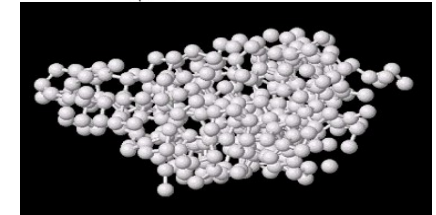
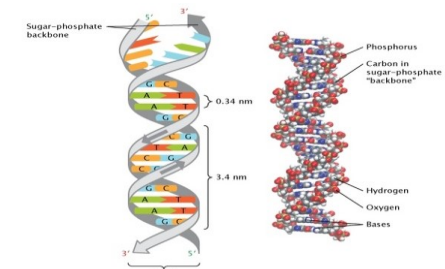


About the same scale of structuration than elementary living matter



Width of DNA  
helix  $\sim 2$  nm

[www.nature.com](http://www.nature.com)



Defects cluster

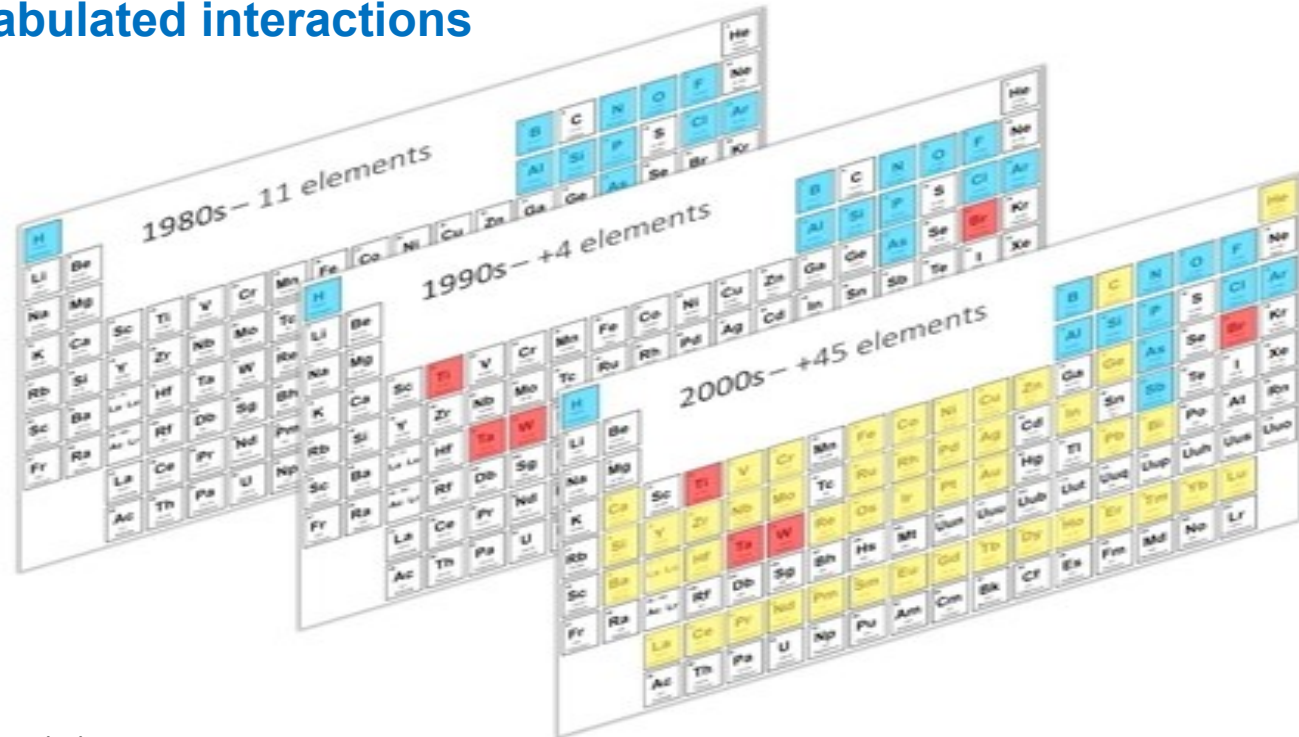
Intel 22 nm node  
gate fin

<http://www.edn.com/Home/PrintView?contentItemId=4395587>



# “New” materials : elements

- A large part of the periodic table is now used in technology
  - ◆ May become a strategic procurement issue (+ ethical and environmental issues)
  - ◆ Large part of non tabulated interactions



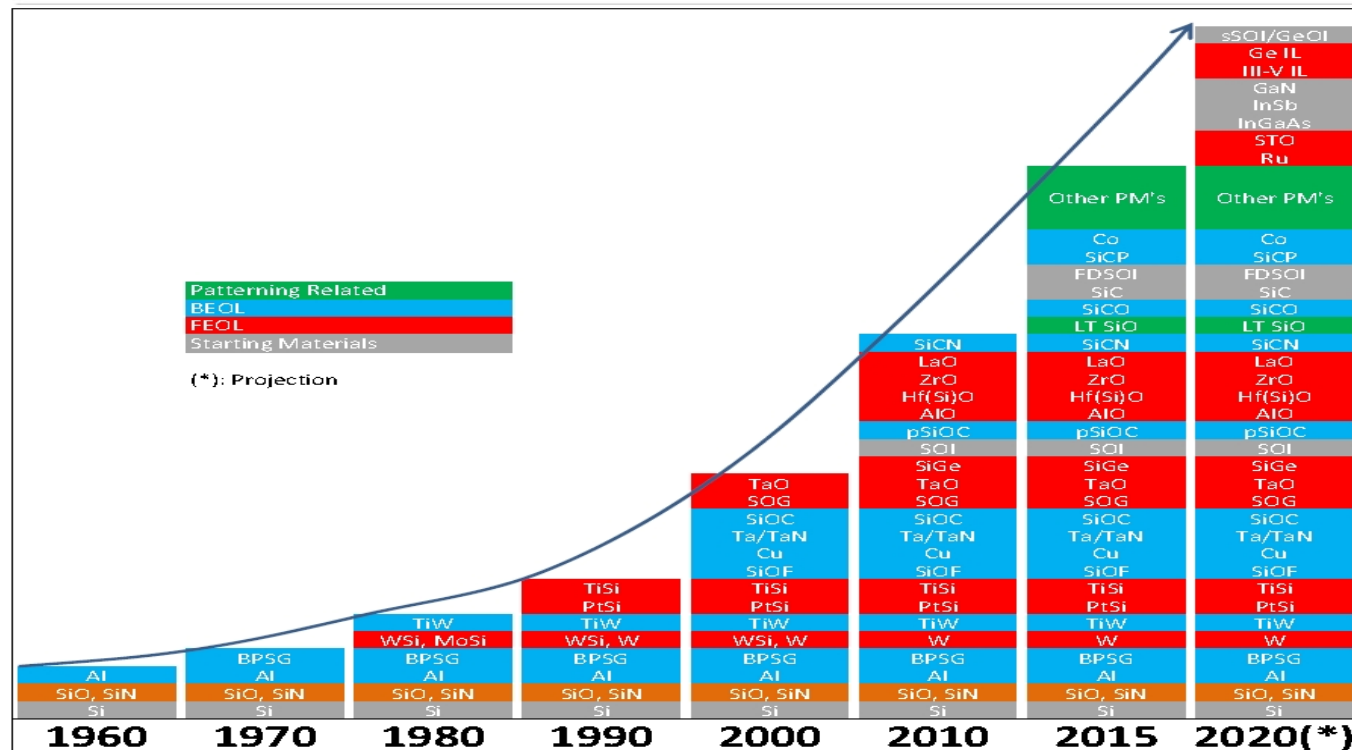
US Securities and Exchange Commission

<https://www.sec.gov/Archives/edgar/data/1101302/000119312516645958/d225180dex991.htm>

# “New” materials : compounds



## MATERIALS INNOVATION



Source: ASM (2015)

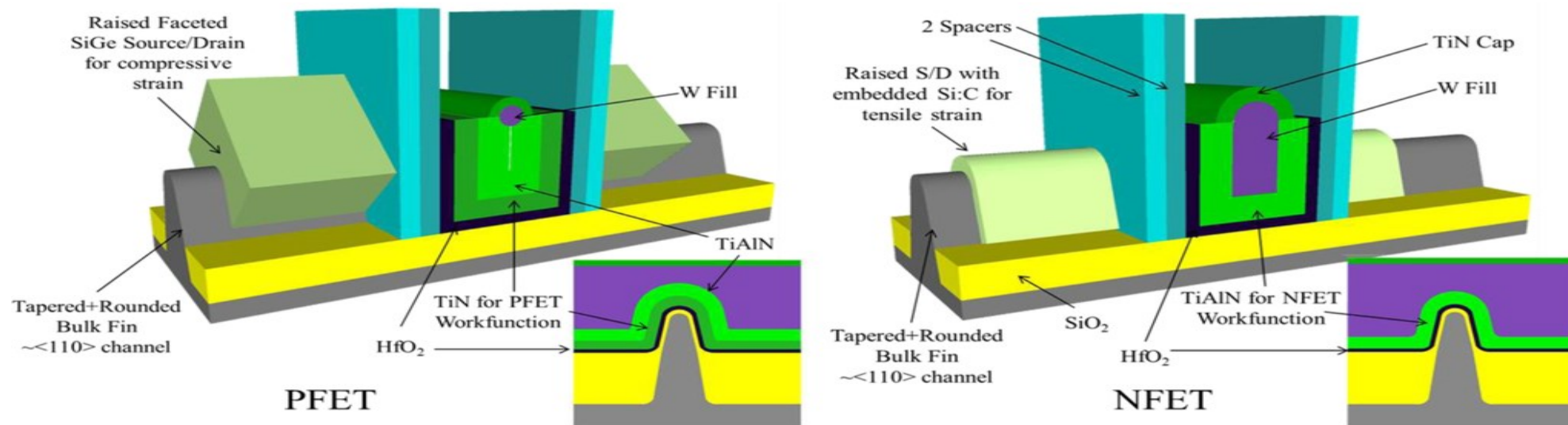
January 12, 2016 | 6

ASM International (American Society for Metals), Electronic Materials Handbook



## ● Intel 22 nm node

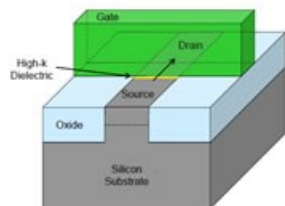
◆ 9 Cu metal layers, W contacts, Ge and C implants



Those technologies are already in your smartphone

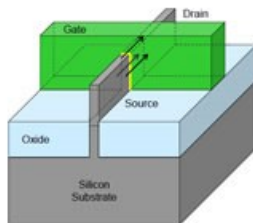
# Complexity : 3D patterns

Traditional Planar Transistor



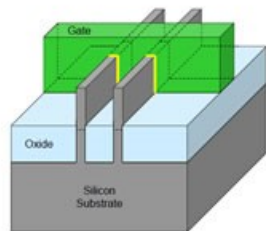
Traditional 2-D planar transistors form a conducting channel in the silicon region under the gate electrode when in the "on" state

22 nm Tri-Gate Transistor



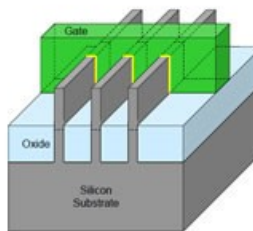
3-D Tri-Gate transistors form conducting channels on three sides of a vertical fin structure, providing "fully depleted" operation

22 nm Tri-Gate Transistor

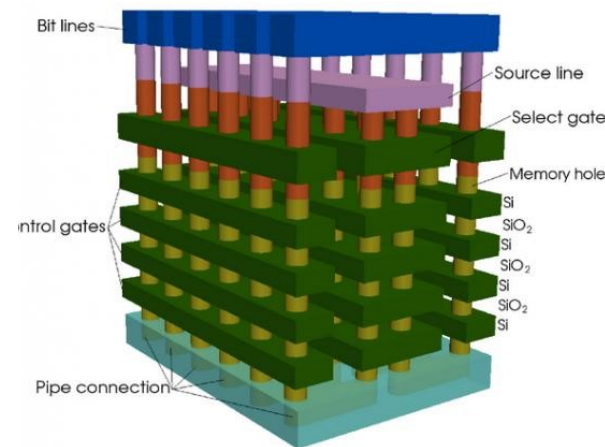
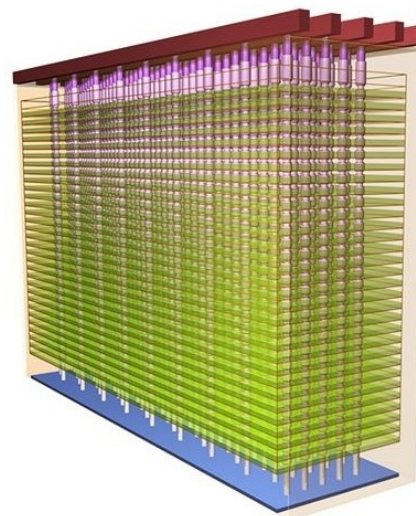
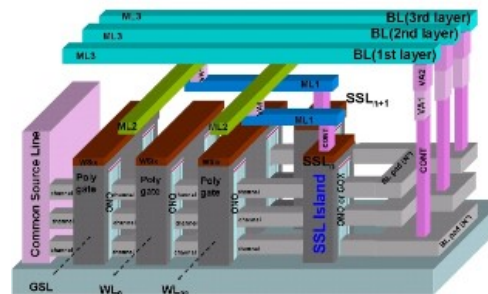


Tri-Gate transistors can have multiple fins connected together to increase total drive strength for higher performance

22 nm Tri-Gate Transistor



Tri-Gate transistors can have multiple fins connected together to increase total drive strength for higher performance

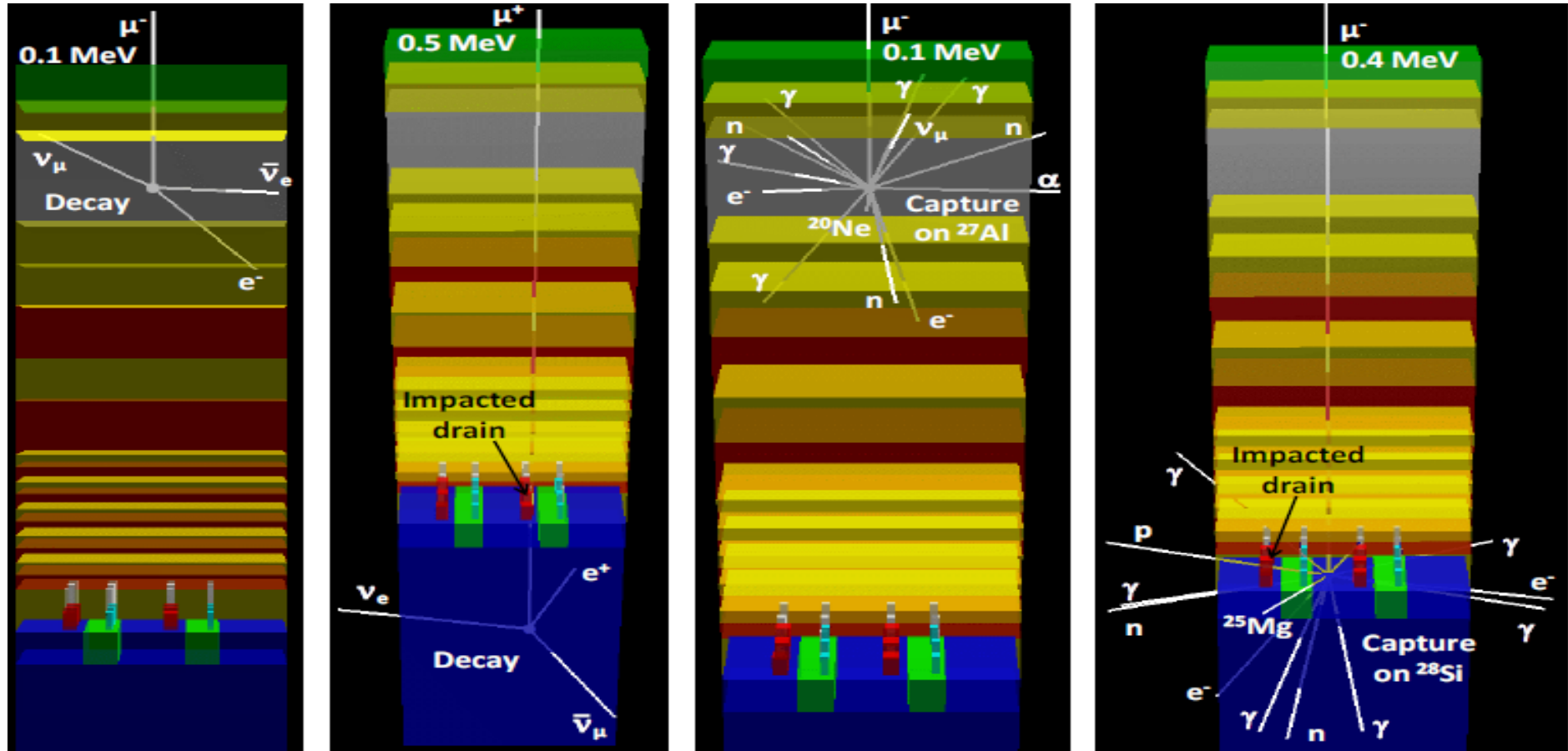


<https://electroiq.com/2012/09/horizontal-channels-key-to-ultra-small-3d-nand/>

<http://www.eenewsanalogue.com/news/toshiba-takes-3d-nand-96-layers-4-bits-cell>

<https://www.notebookcheck.net/Micron-intros-its-first-3D-NAND-memory-for-mobile-devices.171198.0.html>

# Impacts on radiation effects : more interactions



Courtesy Jean-Luc Autran, RADECS 2013 Short Course

# What types of SEE tools do we need ?

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## SEE rate estimations for space projects

- This is an engineering tool, massively used : must be simple and fast
- Extreme accuracy is not needed : SEEs are probabilistic phenomena
  - E.g. IASI mass memory : mean SEU period 90 days, but also 2 events separated by 5 days and 480 days without any event – Poisson law, statistical distribution
- Better have an exhaustive characterization of hazardous events : MBUs, SEFI, HCE, stuck bits, to adapt mitigation techniques

## System-level sensitivity determination

- This is an engineering tool but used to check and eventually improve the robustness of ASIC or other dedicated circuit / system design – typically works at register and function levels

## Technology development, characterization and hardening

- This is an expert tool : needs technology physical information (doping levels, materials, structure, spacing, lay-out, circuit) and detailed particle-matter interaction descriptions – generally uses MC codes such as G4

**Thanks for your attention**